



IRF740ALPBF Information



For Reference Only

Part Number IRF740ALPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 400V 10A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF740ALPBF Specifications

Manufacturer Part Number IRF740ALPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 36nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1030pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1030pF @ 25V Vgs (Max) ### 30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Son (Max) @ Id, Vgs To more of the first of	Manufacturer Part Number	IRF740ALPBF
Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 400V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 36nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1030pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Manufacturer	Vishay Siliconix
PackageTO-262-3 Long Leads, 12Pak, TO-262AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs36nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1030pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs550 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs36nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1030pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs550 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature Supplier Device Package 12PAK Package / Case N-Channel N-Channel NOSFET (Metal Oxide) MOSFET (Metal Oxide) 400V 104 (Tc) 104 (Tc) 105 (10V 107 (10V 103 (10F) 107 (10V 107 (TJ) 108 (Ta), 125W (Tc) 108 (Ta), 125W (Tc) 109 (TJ) 109 (T	Package	TO-262-3 Long Leads, I2Pak, TO-262AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1030pF @ 25V Input Capacitance (Ciss) (Max) @ Vds 1030pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 10A (Tc)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA 36nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case 10A (Tc) 10A (Tc) 10V 10V 4V @ 250μA 36nC @ 10V 1030pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs36nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1030pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs550 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	400V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 36nC @ 10V 1030pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 36nC @ 10V 1030pF @ 25V ±30V 510V 520V 530V 530V 530V 530V 540V 550 mOhm @ 6A, 10V 550 mOhm @ 6A, 10V 550°C (TJ) Through Hole 530PF @ 25V 540PF @ 25V 550 mOhm @ 6A, 10V 550°C (TJ) Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature Cycle Through Hole Supplier Device Package I2PAK Package / Case 1030pF @ 25V 1030p	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	36nC @ 10V
FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	1030pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 550 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs550 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI2PAKPackage / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	3.1W (Ta), 125W (Tc)
Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	550 mOhm @ 6A, 10V
Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	I2PAK
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

IRF740ALPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF740ALPBF Payment Methods





















IRF740ALPBF Shipping Methods













If you have any question about IRF740ALPBF, please do not hesitate to contact us!

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